

2024년 1월 24일(수)-26일(금) | 경주화백컨벤션센터(HICO)

2024년 1월 25일(목), 15:30-17:15 Room I(203),2층

D. Thin Film Process Technology 분과

[TI3-D] Ferroelectrics

좌장: 최병준 교수(서울과학기술대학교), 김건환 교수(연세대학교)

TI3-D-1 15:30-15:45	Mitigation of Field-driven Dynamic Phase Evolution in Ferroelectric Hf _{0.5} Zr _{0.5} O ₂ Films by Adopting Oxygen-supplying Electrode Younghwan Lee ¹ , Se Hyun Kim ² , Hyun Woo Jeong ² , Geun Hyeong Park ² , Jaewook Lee ² , Young Yong Kim ³ , and Min Hyuk Park ^{1,2} ¹ Research Institute of Advanced Materials, Seoul National University, ² Department of Materials Science and Engineering, Seoul National University, ³ Beamline Division, Pohang Accelerator Laboratory
TI3-D-2 15:45-16:00	Interface Engineering for Enhancement of Ferroelectricity in Sub-5 nm Ultrathin Hf _{0.5} Zr _{0.5} O ₂ Films Se Hyun Kim ¹ , Younghwan Lee ² , Dong Hyun Lee ¹ , and Min Hyuk Park ^{1,2} ¹ Department of Mcrystaterials Science and Engineering, Seoul National University, ² Research Institute of Advanced Materials, Seoul National University
TI3-D-3 16:00-16:15	SynergisticImpactofAl2O3CappingLayerandDepositionTemperature for Enhancing the Ferroelectricity of Undoped HfO2ThinFilmsSang Han Ko and Sung Min YoonDepartment of Advanced Materials Engineering for Information and Electronics,Kyung Hee University
TI3-D-4 16:15-16:30	CF ₄ Plasma Passivation on Laminated-ALD HZO MFIS-FeFET Kyungsoo Park ¹ , Chulwon Chung ² , Boncheol Ku ¹ , Seung Hyeon Yun ¹ , Junhyeok Park ¹ , Yu Jeong Choi ¹ , and Changhwan Choi ¹ ¹ Division of Materials Science and Engineering, Hanyang University, ² Deparment of Energy Engineering, Hanyang University
TI3-D-5 16:30-16:45	Development of Lab-Scale Pulsed Laser Annealing (PLA) System for Hf _x Zr _{1-x} O ₂ Thin Film Crystallization Hyeonsik Kim ^{1,2} , Hyojin Yang ² , Sejun Park ² , Jong-Ho Bae ² , and Inhee Cho ¹ ¹ Korea-Russia Innovation Center, KITECH, ² School of Electrical Engineering, Kookmin University

제 31회 한국반도체학술대회 The 31st Korean Conference on Semiconductors

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TI3-D-6	Ferroelectricity of Hf _{0.5} Zr _{0.5} O ₂ Thin Film Induced at 350 °C by Thermally
	Accelerated Nucleation during Atomic Layer Deposition Jaewook Lee ^{1,2} , Se Hyun Kim ^{1,2} , Younghwan Lee ³ , Sang-Youn Park ⁴ , and Min
16:45-17:00	yuk Park ^{1,2,3} Department of Materials Science and Engineering, Seoul National Universit nter-University Semiconductor Research Center, Seoul National Universit Research Institute of Advanced Materials College of Engineering, Seoul Nation niversity, ⁴ Pohang Accelerator Laboratory, POSTECH
	The Impact of CF4 Plasma Treatment on the Performance of
TI3-D-7	HfO ₂ /IGZO Thin film Transistors (TFTs)
17:00-17:15	Gyu Lee Kim, Sun bum Kim, Chan seul Lee, and Changhwan Choi
	Division of Materials Science and Engineering, Hanyang University